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Retraction: Enhanced resistive switching memory characteristics and mechanism using a Ti nanolayer at the W/TaOx interface

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Retraction

This article is retracted.

The journal editors would like to apologise for the early publication of the original article [1], which is being retracted as it was published prior to the completion of essential revisions.

The revised version of this article has now been published, and is available online [2].

References
1. Prakash A, Maikap S, Chiu HC, Tien TC, Lai CS: **Enhanced resistive switching memory characteristics and mechanism using a Ti nanolayer at the W/TaOx interface.** *Nanoscale Research Letters* 2013, **9**:152.
2. Prakash A, Maikap S, Chiu HC, Tien TC, Lai CS: **Enhanced resistive switching memory characteristics and mechanism using a Ti nanolayer at the W/TaOx interface.** *Nanoscale Research Letters* 2014, **9**:125.

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